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熔融先驱体法制备连续 SiC 自由薄膜
及其结构与发光特性研究

Synthesis, Microstructure and Photoluminescence Properties
of Continuous Freestanding Silicon Carbide Films by Melt
Spinning of Precursor

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**Synthesis, Microstructure and Photoluminescence
Properties of Continuous Freestanding Silicon Carbide
Films by Melt Spinning of Precursor**



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the Requirements for the Degree of
Doctor Philosophy

By

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目 录

摘 要	I
Abstract	III
主要创新和贡献	VI
第一章 绪论	1
1.1 引言	1
1.2 SiC 材料的基本性质	2
1.2.1 结构特征	2
1.2.2 理化性质	3
1.2.3 SiC 半导体的特性	5
1.3 SiC 半导体材料的发展与应用	8
1.3.1 发展进程	8
1.3.2 应用现状与前景	10
1.4 SiC 半导体材料的制备方法	15
1.4.1 SiC 体单晶材料的制备方法	15
1.4.2 SiC 薄膜的制备方法	16
1.5 SiC 薄膜面临的问题	24
1.5.1 SiC 薄膜的外延工艺	24
1.5.2 SiC 薄膜的发光性能	25
1.5.3 SiC 薄膜的发光机理	26
1.6 本文的选题依据与研究目标	29
1.6.1 选题依据	29
1.6.2 研究目标	31
1.7 研究思路	32
1.8 研究内容	33
参考文献	34
第二章 实验方法	49
2.1 先驱体熔融纺膜法制备连续 SiC 自由薄膜	49
2.1.1 先驱体的合成	49
2.1.2 先驱体的熔融纺膜	49
2.1.3 不熔化处理	50
2.1.4 高温裂解	50
2.2 实验原材料与仪器设备	51

2.3 SiC 薄膜的主要表征方法	52
2.3.1 结构表征	52
2.3.2 组分分析	56
2.3.3 缺陷态测量	57
2.3.4 性能测试	58
参考文献	60
第三章 连续 SiC 自由薄膜的制备研究	61
3.1 先驱体的合成及其发光性能	61
3.1.1 样品制备	63
3.1.2 测试与表征	64
3.1.3 结果与讨论	64
3.2 自制实验装置及其简要工作原理	69
3.2.1 喷膜装置的设计与制作	69
3.2.2 定位进样取样器的设计与制作	71
3.2.3 万能试验机夹具的设计与制作	71
3.3 连续 SiC 自由薄膜的制备与表征	72
3.3.1 样品制备	72
3.3.2 测试与表征	73
3.4 连续 SiC 自由薄膜实验结果及讨论	73
3.4.1 连续 PCS 原膜	73
3.4.2 薄膜厚度分析	74
3.4.3 氧化交联 FTIR 结构分析	74
3.4.4 薄膜组分分析	76
3.4.5 薄膜 SEM 分析	77
3.4.6 微观结构分析	78
3.4.7 物理性质分析	79
3.4.8 光致发光性质分析	80
3.4.9 讨论分析	80
3.5 本章小结	82
参考文献	83
第四章 连续 SiC 自由薄膜发光特性与机理分析	86
4.1 氧化交联时间对连续 SiC 自由薄膜发光强度的影响	87
4.1.1 不同氧化交联时间的样品制备	87
4.1.2 FTIR 结构分析	88
4.1.3 XRD 物相分析	89

4.1.4 Raman 光谱分析.....	90
4.1.5 XPS 分析.....	90
4.1.6 发光特性分析.....	95
4.1.7 薄膜 SEM 分析.....	96
4.1.8 薄膜 TEM 分析.....	97
4.1.9 薄膜结构模型的建立.....	98
4.1.10 缺陷态分析.....	99
4.1.11 讨论分析.....	99
4.2 裂解温度对连续 SiC 自由薄膜发光强度的影响.....	100
4.2.1 不同裂解温度的样品制备.....	100
4.2.2 FTIR 结构分析.....	101
4.2.3 热重分析.....	102
4.2.4 发光特性分析.....	103
4.2.5 缺陷态分析.....	104
4.2.6 讨论分析.....	105
4.3 发光机理分析与发光模型的建立.....	106
4.4 本章小结.....	111
参考文献.....	112
第五章 连续 SiC 自由薄膜高温环境稳定性与热氧化研究.....	116
5.1 自制实验装置及其简要工作原理.....	117
5.1.1 高温环境模拟气氛处理系统的建立.....	118
5.1.2 高温气氛热处理装置的建立.....	119
5.2 连续 SiC 自由薄膜高温氧化的热力学研究.....	121
5.2.1 计算方法.....	121
5.2.2 结果与讨论.....	122
5.3 空气中热氧化性实验研究.....	127
5.3.1 空气气氛中高温退火处理.....	127
5.3.2 测试与表征.....	127
5.3.3 实验及结果分析.....	127
5.4 水氧处理实验研究.....	131
5.5 连续 SiC 自由薄膜的高温氧化动力学模型.....	132
5.5.1 薄膜在空气中的氧化动力学模型.....	132
5.5.2 薄膜在水氧中的氧化动力学模型.....	134
5.5.3 实验验证与讨论.....	137
5.6 连续 SiC 自由薄膜的热氧化工艺.....	140

5.6.1 热氧化工艺比较	140
5.6.2 薄膜的热氧化工艺	141
5.6.3 实验结果与讨论	141
5.7 本章小结	142
参考文献	143
第六章 连续 SiC(Al)自由薄膜的制备及其微观结构与发光特性	146
6.1 连续 SiC(Al)自由膜的制备	146
6.2 测试与表征	147
6.3 实验结果与分析	147
6.3.1 氧化交联 FTIR 结构分析	147
6.3.2 薄膜 SEM 分析	149
6.3.3 薄膜成分分析	150
6.3.4 微观结构分析	151
6.3.5 光致发光分析	155
6.3.6 讨论分析	155
6.4 连续 SiC(Al)自由膜的微观结构与发光机制	156
6.4.1 不同裂解温度的样品制备	156
6.4.2 FTIR 结构分析	157
6.4.3 薄膜 SEM 分析	159
6.4.4 薄膜成分分析	159
6.4.5 微观结构分析	160
6.4.6 薄膜的高温热力学相变	166
6.4.7 薄膜结构模型的建立	167
6.4.8 发光特性分析	170
6.4.9 发光机理分析	171
6.5 本章小结	172
参考文献	173
第七章 总结与展望	175
7.1 结论	175
7.2 展望	176
攻读博士期间发表的论文情况	178
致 谢	181

Contents

Abstract in Chinese	I
Abstract in English	III
Innovation and contribution	VI
1 Introduction	1
1.1 Introduction	1
1.2 Basic properties of SiC	2
1.2.1 Structural properties	2
1.2.2 Physicochemical properties	3
1.2.3 SiC semiconductor characteristic	5
1.3 Development and application of SiC semiconductor	8
1.3.1 Development process	8
1.3.2 Application status and prospect	10
1.4 Preparation methods of SiC semiconductor	15
1.4.1 Preparation methods of SiC bulk single crystal	15
1.4.2 Preparation methods of SiC films	16
1.5 Facing problems of SiC films	24
1.5.1 Epitaxial process of SiC films	24
1.5.2 Luminescent properties of SiC films	25
1.5.3 Luminescent mechanism of SiC films	26
1.6 Research background and objectives	29
1.6.1 Research background	29
1.6.2 Research objectives	31
1.7 Research methods	32
1.8 Research contents	33
References	34
2 Experimental	49
2.1 Melt spinning of precursors	49
2.1.1 Preparation of precursors	49
2.1.2 Melt spinning	49
2.1.3 Curing	50
2.1.4 Pyrolysis	50
2.2 Materials and apparatus	51
2.3 Characterization methods for SiC films	52
2.3.1 Structural research	52
2.3.2 Composition analysis	56
2.3.3 Defect states measurement	57
2.3.4 Performance test	58

References	60
3 Studies on fabrication of continuous freestanding SiC films	61
3.1 Synthesis and photoluminescence properties of precursors	61
3.1.1 Sample preparation	63
3.1.2 Testing and characterization	64
3.1.3 Results and discussion	64
3.2 Experimental apparatus and its principle	69
3.2.1 Melt spinning device for PCS and its principle	69
3.2.2 The apparatus for sampling continuous freestanding SiC films	71
3.2.3 Tensile testing device for continuous freestanding SiC films	71
3.3 Synthesis and characterization of continuous freestanding SiC films	72
3.3.1 Sample preparation	72
3.3.2 Testing and characterization	73
3.4 Results and discussion	73
3.4.1 Continuous freestanding PCS green films	73
3.4.2 Analysis of the thickness of the films	74
3.4.3 FTIR analysis for PCS green films before and after curing	74
3.4.4 Composition analysis	76
3.4.5 Characterization of morphology	77
3.4.6 Characterization of microstructure	78
3.4.7 Physical properties	79
3.4.8 Photoluminescence properties	80
3.4.9 Discussion	80
3.5 A summary of the findings	82
References	83
4 Blue-emitting mechanisms of continuous freestanding SiC films	86
4.1 Effect of oxidation curing time on the PL intensity of SiC films	87
4.1.1 Sample preparation	87
4.1.2 FTIR analysis of structure	88
4.1.3 XRD phase analysis	89
4.1.4 Raman spectroscopy analysis	90
4.1.5 XPS analysis	90
4.1.6 Photoluminescence properties	95
4.1.7 SEM analysis	96
4.1.8 TEM analysis	97
4.1.9 Model proposed for the structure of SiC films	98
4.1.10 Defect states analysis	99
4.1.11 Discussion	99
4.2 Effect of pyrolysis temperatures on the PL intensity of SiC films	100
4.2.1 Sample preparation	100

4.2.2 FTIR analysis of structure	101
4.2.3 TG analysis	102
4.2.4 Photoluminescence properties	103
4.2.5 Defect states analysis.....	104
4.2.6 Discussion.....	105
4.3 Photoluminescence mechanism and wide band model for SiC films.....	106
4.4 A summary of the findings	111
References	112
5 High-temperature environmental stability and thermal oxidation process of continuous freestanding SiC films	116
5.1 Experimental apparatus and its principle	117
5.1.1 High temperature furnace and the water vapor saturator at atmospheric pressure.....	118
5.1.2 High temperature furnace and sample loading stage.....	119
5.2 Thermodynamic calculations for high-temperature oxidation of SiC films.....	121
5.2.1 Thermodynamic calculation method.....	121
5.2.2 Results and discussion.....	122
5.3 Influence of annealing temperature on the structure and photoluminescence properties of continuous freestanding SiC films in air.....	127
5.3.1 Annealing treatment in air.....	127
5.3.2 Testing and characterization.....	127
5.3.3 Results and analysis.....	127
5.4 Oxidation behaviors of SiC films annealed in wet oxidizing environments ...	131
5.5 High temperature oxidation kinetic model of SiC films	132
5.5.1 Oxidation kinetic model of SiC films annealed in air	132
5.5.2 Oxidation kinetic model of SiC films annealed in wet-air	134
5.5.3 Experimental verification and discussion.....	137
5.6 Thermal oxidation process of continuous freestanding SiC films.....	140
5.6.1 Comparison of thermal oxidation process.....	140
5.6.2 Thermal oxidation process	141
5.6.3 Results and discussion.....	141
5.7 A summary of the findings	142
References	143
6 Synthesis, microstructure and photoluminescence properties of continuous freestanding SiC(Al) films.....	146
6.1 Sample preparation.....	146
6.2 Testing and characterization	147
6.3 Results and analysis.....	147
6.3.1 FTIR analysis of structure	147

6.3.2 SEM analysis	149
6.3.3 Composition analysis.....	150
6.3.4 Microstructure analysis	151
6.3.5 Photoluminescence properties	155
6.3.6 Discussion.....	155
6.4 Microstructure and photoluminescence mechanism of continuous freestanding SiC(Al) films	156
6.4.1 Sample preparation	156
6.4.2 FTIR analysis of structure	157
6.4.3 SEM analysis	159
6.4.4 Composition analysis.....	159
6.4.5 Microstructure analysis	160
6.4.6 Thermodynamic calculations and phase stabilities	166
6.4.7 Model proposed for the structure.....	167
6.4.8 Photoluminescence properties	170
6.4.9 Photoluminescence mechanism.....	171
6.5 A summary of the findings	172
References	173
7 Conclusion and prospect.....	175
7.1 Conclusion.....	175
7.2 Prospect	176
Published papers during learning terms	178
Acknowledgements.....	181

摘要

SiC作为第三代宽带隙半导体材料因具有禁带宽度大、热导率高、耐高温、抗辐射、机械强度大和化学稳定性好等特性而成为制作高温、高频、大功率和极端条件下半导体器件的理想材料,已广泛应用于微机电系统(MEMS)、短波光电子器件及发光二极管等领域。由于制备SiC体单晶困难且昂贵, SiC薄膜的异质外延生长显得尤为重要,但目前外延生长SiC薄膜均借助基材进行沉积,存在晶格和热膨胀系数失配等问题,导致界面处存在因应力失配而引起的大量缺陷,使其发光效率降低,使用寿命缩短。因此,有必要寻求无界面缺陷的SiC薄膜制备工艺与方法。此外, SiC薄膜是较好的蓝光发射材料,但其属于间接跃迁半导体,发光效率较低是制约其在发光器件中应用的主要障碍,虽然已发现多孔、无定形、纳米及掺杂改性的SiC能提高其发光效率,也用量子限制效应、表面模型与缺陷态模型等来解释其发光机理,但对于SiC薄膜材料发光性能的提高及其发光机制的考察尚显不足,仍需进一步深入研究与探索。

本文基于先驱体熔融纺膜法的技术,以聚碳硅烷(PCS)和聚铝碳硅烷(PACS)为原料,通过自行设计的喷膜装置熔融纺出连续PCS、PACS自由薄膜,并对其不熔化预处理与高温裂解制得系列连续SiC自由薄膜,结合微观结构及光谱学分析对其进行了发光特性与发光机理研究,深入研究了交联条件、掺杂、烧结条件及退火温度等工艺对薄膜理化性能和微结构演变的影响及其关键控制因素,阐明了薄膜形成的微观机制及发光机理。研究结果为新型强光发射SiC薄膜的质量控制和组分、微结构的创新设计提供了依据,为其在蓝色发光器件、紫外光敏器件及MEMS等高新技术领域的应用提供了有效的技术支撑。主要研究内容及结果如下:

- 1、合成了不同异质元素的先驱体,发现其在360-450 nm范围有较强的蓝紫光发射特性。其中, PACS的发光强度最大,含镓PCS次之,并探明了先驱体的发光机理;采用自制喷膜装置与先驱体熔融纺膜法技术制备出了新型连续SiC自由薄膜,具有成本低、工艺简单,可工程化及结构功能一体化等特点。薄膜具有厚度与成分可控、可避免晶格和热膨胀系数失配问题。波长375 nm激发下,在410-450 nm范围有较强的蓝光发射。

- 2、研究了不熔化预处理及高温裂解对薄膜发光特性的影响机制,并考察了样品的界面微结构演变和发光机制。结果表明:(1) 交联时间越长,氧含量越高,

SiO_xC_y和游离碳增加, β-SiC晶粒减小; (2) 薄膜在410-450 nm范围内有较强的蓝光发射, 1200 °C烧结的薄膜随交联时间增加, 发光强度增大; 而1300 °C样品其发光强度相对下降; (3) 412 nm与435 nm附近的发光峰为界面富含的氧空位和双氧空位缺陷态构成发光中心, 电子在β-SiC晶粒中受到受激发后, 价带被激发到导带, 与空穴形成电子-空穴对隧穿到晶体表面驰豫到带尾, 而被氧空位缺陷态俘获, 发生辐射复合而产生了蓝光发射。(4) 由于量子表面效应与缺陷态共同作用, 交联10 h于1150 °C烧结的薄膜发光强度较高。随着温度升高, 由于SiO_xC_y高温分解在薄膜本体内留下较多缺陷, 导致更多非辐射中心, 发光强度明显减弱, 甚至猝灭。

3、评价了连续 SiC 自由薄膜在高温环境下稳定性能以及微观结构演变。(1) 建立了一套连续 SiC 自由薄膜高温环境模拟气氛处理系统; (2) 建立了 Ar-Si-C-O-H 数据库并进行热力学计算, 证明薄膜在高温环境中主要存在惰性氧化; (3) 连续 SiC 自由薄膜独特的性质可在表面形成一层连续的 SiO₂ 氧化层。随着退火温度的升高, 薄膜的抗氧化和发光特性略有降低, 薄膜中无定型 SiO_xC_y 减少, β-SiC 晶粒长大及游离碳增多, 薄膜表面硬度与电阻率下降; (4) 建立了 SiC 薄膜在空气与水氧环境下的高温氧化动力学模型, 并对其热氧化工艺进行优化。

4、从原料的合成阶段引入 Al 掺杂改性, 制备了连续 SiC(Al)自由薄膜, 并对其结构与发光特性进行了研究。利用微观结构观察与光谱学表征相结合阐明了含 Al 相在薄膜的作用、状态和存在位置。结果表明: (1) 薄膜具有近化学计量比, 含有 β-SiC 晶粒、α-SiC 晶粒、碳簇以及少量的氧和铝; (2) Al 作为烧结助剂, 对改善薄膜结构致密度, 控制晶粒长大的作用十分明显。但其作用受交联时间、烧结温度和晶粒尺寸等因素的影响; (3) 交联 3 h 并于 1800 °C 烧成薄膜具有较高的致密度和较强的发光特性, 在室温下表现出了 380-500 nm 宽谱带发光, 其 420 nm 处的发光峰可归因于 β-SiC 位错与层错的缺陷工程以及 α-SiC 晶格的缺陷, 而 440 nm 处则源于晶体界面、游离碳和多孔存在; (4) 氧主要以 Al₄O₄C 相存在, 铝以 Al₄SiC₄ 与 Al₄O₄C 两相形式存在, 在高温条件下均能抑制薄膜中晶粒长大的作用。结合结构分析与热力学计算结果并最终建立了连续 SiC(Al)自由薄膜的结构模型。

关键词: 先驱体法; 熔融纺膜; 连续 SiC 自由薄膜; 连续 SiC(Al)自由膜; 光致发光

Abstract

Silicon carbide (SiC) films exhibit several advantages such as wide band gap, good radiation resistance, high thermal conductivity, superior mechanical strength and chemical inertness. These unique properties endow SiC films with great potential for applications in the power microelectromechanical systems (MEMS) in harsh environments, high-temperature electronic and optoelectronic devices applications (light emitting diodes). The heteroepitaxy of the SiC films is very important since high quality SiC wafer is expensive and hardly to be achieved. However, the performance of the heteroepitaxial SiC films is often dependent on the film/substrate interaction due to the mismatches of thermal expansion coefficient and lattice constant at the interface. And residual strain accumulated at the interface can lead to warping problems. Therefore, there has been a considerable amount of interest in the development of alternative technique for producing SiC films which may avoid the significant difference of the thermal expansion coefficients between SiC and substrate.

SiC films are also explored as one of the most outstanding blue luminescent materials, but they can not emit light efficiently enough at room temperature due to their indirect band gaps. Recently, amorphous SiC, porous crystalline SiC, nanometer SiC and doped SiC have been reported to improve the blue luminescent efficiency and stability. Several models have been proposed to explain the luminescence, such as quantum confinement, surface states and defect states. However, the luminescent efficiency is still too low to be used in actual devices, and the origin of the observed light emission was not clear. Thus, further experimental and theoretical investigations were needed to address this issue.

In this thesis, a novel technique based on melt spinning of precursor was introduced to produce continuous freestanding SiC films. The Polycarbosilane (PCS) and Polyaluminocarbosilane (PACS) precursors were deaerated, melt spun, crosslinked and pyrolyzed at high temperature in order to convert the initial precursors into freestanding SiC films. The photoluminescence (PL) properties and mechanism of samples were demonstrated through their microstructure and spectroscopy analysis. Effects of oxidation time, doping, sintering and annealing temperatures on the physicochemical properties and microstructural evolution of the SiC films were further investigated. Much of analysis and discussion will then reveal the factors related to the PL properties and microstructural evolution of the films. The obtained results would

help to explore the SiC blue-emitting mechanisms and facilitate the application of SiC films in advanced optoelectronic devices, MEMS and such complex shaped-materials. The main subjects and results are summarized as follows:

1. PCS and doped PCS precursors were prepared using a one-pot method. The PL spectrum of precursors showed a wide luminescence band from 360 nm to 450 nm, and the origin of PL was also investigated. Comparing PL spectra of different samples, it was revealed that the PL intensity from the PACS was larger than that from the PCS and Dy-PCS. The dense and continuous freestanding SiC films were first synthesized using the novel technique of melt spinning of PCS precursor. An equipment consisted of spinneret, mandril, tank, seal cover and seal groove was successfully set up for melt spinning. In comparison with heteroepitaxy process, the freestanding films could avoid mismatches of thermal expansion coefficient and lattice constant at the interface between SiC coatings and substrate. The thickness of the films ranged from 8 μm to 190 μm depending on the spout size of spinneret mouth and spinning speed. The PL spectra of films appeared in the visible light range and had a broad spectra feature with two blue peaks at 416 nm and 435 nm under 375 nm excitation of a Xe lamp.

2. Effects of curing time and pyrolysis temperature on the PL properties of SiC films were demonstrated. The interface structural evolution and PL mechanism were also examined. The results and conclusions were as follows: (1) By increasing the curing time, the oxygen, SiO_xC_y and free carbon content enhanced as the size of β -SiC grains decreased. (2) The PL spectra showed two strong blue emissions at 416 nm and 435 nm, which were unchanged neither with oxygen content nor with β -SiC crystallite size. The PL intensity enhanced with increasing curing time when sintered at 1200 °C. However, a reversed trend was identified after the films were sintered at 1300 °C. (3) Spectroscopy and microscopy studies provided the evidences that photoexcitation occurred in the β -SiC nano-crystals cores, while photoexcited electrons and holes in the β -SiC nano-crystals transferred into the oxygen mono- and di-vacancy defect centers from SiO_xC_y surrounding the β -SiC nano-crystals and radiatively recombine there. (4) The higher PL intensity of samples cured for 10 h and sintered at 1150 °C was attributed to quantum surface effect and defect states. But too many flaws caused by the decomposition of SiO_xC_y at elevated temperature. And the flaw content increased with the rise of sintering temperature, more complex quenching defects and therefore nonradiative recombination were formed. The PL efficiency declined, evidently.

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